

FORM PTO-1449  
(REV. 7.80)

JAN 08 2002

U.S. DEPARTMENT OF COMMERCE  
PATENT AND TRADEMARK OFFICE

ATTY. DOCKET NO. 119941-1089

SERIAL NO.: 09/820,2446

LIST OF PRIOR ART CITED BY APPLICANT  
(Use several sheets if necessary)

APPLICANT: Kanakasbapathy, et al.

FILING DATE: March 28, 2001

GROUP: 1765

## U. S. PATENT DOCUMENTS

*EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (if appropriate)
LV	4,747,922	5/31/88	Sharp	204	192.11	3/25/86
	4,963,239	10/16/90	Shimamura et al.	204	192.12	1/26/89
	5,423,915	06/13/95	Murata, et al.	118	723	09/28/93
	5,435,886	07/25/95	Fujiwara, et al.	156	643	05/23/94
	5,436,172	07/25/95	Moslehi	437	8	05/28/91
	5,453,305	09/26/95	Lee	427	562	09/02/93
	5,467,013	11/14/95	Williams, et al.	324	127	12/07/93
	5,472,561	12/05/95	Williams, et al.	156	627	03/27/95
	5,510,011	4/23/96	Okamura et al.	204	192.3	12/22/94
	5,540,824	07/30/96	Yin et al.	156	345	07/18/94
	5,554,853	09/10/96	Rose	250	492	03/10/95
	5,558,718	09/24/96	Leung	118	723	04/08/94
	5,580,419	12/03/96	Berenz	156	628	02/23/94
	5,580,429	12/03/96	Chan, et al.	204	192	06/07/95
	5,607,509	03/04/97	Schumacher, et al.	118	723	04/22/96
	5,619,103	04/08/97	Tobin, et al.	315	111	06/07/95
	5,650,032	07/22/97	Keller, et al.	156	345	06/06/95
LV	5,683,548	11/04/97	Hartig, et al.	156	643	02/22/96

OTHER PRIOR ART (Including Author, Title, Date, Pertinent Pages, Etc.)

(CONTINUED ON PAGE TWO)

EXAMINER

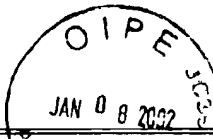
LAN VINH

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\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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U. S. PATENT DOCUMENTS							
*EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (If Approp.)
LV		5,728,261	3/17/98	Wolfe et al.	156	662.1	5/26/95
		5,868,897	2/9/99	Ohkawa	156	345	9/18/96
		5,968,377	10/19/99	Yuasa et al.	219	121.41	5/22/97
		5,983,828	11/16/99	Savas	118	723 1	10/8/96
		5,783,102	07/21/98	Keller	216	68	02/05/96
		5,846,375	12/08/98	Gilchrist, et al.	156	345	09/26/96
LV		6,028,285	02/22/00	Khater, et al.	219	121	11/19/97
FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES NO
OTHER PRIOR ART (Including Author, Title, Date, Pertinent Pages, Etc.)							
LV	Kanakasabapathy, Sivananda K., Overzet, Lawrence J., and Midha, Vikas and Economou, Demetre Alternating Fluxes of Positive and Negative Ions from Ion-Ion Plasma, University of Texas at Dallas, and University of Houston, 2000, pp1-8 and figures 1-3						
LV	Koromogawa, Takashi, Fujii, Takashi, Yamashita, Akihito, Horiike, Yasuhiro, and Shindo, Haruo, Negative Ion Assisted Silicon Oxidation in Downstream of Microwave Plasma, Tokai University, Hiratsuka, Japan and Toyo University, Kawagoe, Japan, 1998 Publication Board, Japanese Journal of Applied Physics, Part 1, No. 9A, September 1998, Jpn. J. Appl. Phys. Vol. 37 (1998) pp5028-5032						
LV	Samukawa, Seiji, Highly Selective and Highly Anisotropic SiO <sub>2</sub> Etching in Pulse-Time Modulated Electron Cyclotron Resonance Plasma, NEC Corporation, Ibaraki, Japan, Part 1, No. 48, April 1994, Jpn. J. Appl. Phys. Vol. 33 (1994) pp2133-2138						
LV	Ohtake, Hiroto and Samukawa, Seiji, Charge-free etching process using positive and negative ions in pulse-time modulated electron cyclotron resonance plasma with low-frequency bias, NEC Corporation, Ibaraki, Japan Appl. Phys. Lett. 68 (17), 22 April 1996, pp2416-2417						
LV	Ahn, Tae Hyuk, Nakamura, Keiji and Sugai, Hideo, A New Technology for Negative Ion Detection and the Rapid Electron Cooling in a Pulsed High-Density Etching Plasma, Nagoya University, Nagoya, Japan, Part 2, No. 10B, 15 October 1995, Jpn. J. Appl. Phys. Vol. 34 (1995) pp L1405-L1408						
LV	Hashimoto, Koichi, Hikosaka, Yukinobu, Hasegawa, Akihiro and Nakamura, Moritaka, Reduction of Electron Shading Damage Using Synchronous Bias in Pulsed Plasma, Fujitsu Limited, Kawasaki, Japan, Part 1, No. 6A, June 1996, Jpn. Appl. Phys. Vol. 35 (1996) pp3363-3368						
LV	Overzet, L.J. and Luo, L., Negative and positive ions from radio frequency plasmas in boron trichloride, University of Texas at Dallas, Appl. Phys. Lett. 59 (2), 8 July 1991, pp161-163						
LV	Samukawa, Seiji and Terada, Kazuo, Pulse-time modulated electron cyclotron resonance plasma etching for highly selective, highly anisotropic, and less-charging polycrystalline silicon patterning, NEC Corporation, Ibaraki, Japan, J. Vac. Sci. Technol. B 12(6), Nov/Dec 1994, pp3300-3305						
LV	Samukawa, Seiji, Pulse-time modulated electron cyclotron resonance plasma etching with low radio-frequency substrate bias, NEC Corporation, Ibaraki, Japan, Appl. Phys. Lett., Vol. 68, No. 3, 15 January 1996, pp316-318						
LV	Overzet, L.J., Beberman, J.H. and Verdeyen, J.T., Enhancement of negative ion flux to surfaces from radio-frequency processing discharges, University of Illinois, J. Appl. Phys. 66 (4), 15 August 1989, pp1622-1631						
EXAMINER: LAN VINH				DATE CONSIDERED 1/28/2004			
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